IN THE SPECIFICATION

Please replace the paragraph at page 4, line 19 to page 5, line 7, with the following rewritten paragraph:

The capacitance of the capacitor is proportional to the permittivity of a thin film disposed between the electrodes and area of an opposed electrode, and inversely proportional to a distance between the electrodes disposed opposite to each other. A leakage current flows through the tunnel insulating film through which the electric charge is passed for write/erase, and the write/erase is inhibited. Therefore, a method of increasing a contact area of the gate insulating film with the floating gate FG, and control gate CG is usually used in order to increase Cip. For example, a slit width is reduced to enlarge the width (dimension 1a shown in FIG. 24) of the upper surface of the floating gate FG. Alternatively, a technique of increasing the film thickness of the floating gate FG to increase a length (dimension 1b shown in FIG. 24) of a side wall of the floating gate FG has been developed. However, as a result, it is necessary to excessively reduce a slit processed dimension as compared with a gate or wiring material. Moreover, when the film thickness of the floating gate FG is increased, it is increasingly difficult to process the gate. Furthermore, with the miniaturization, the parasitic capacitance between FG and FG disposed opposite to each other between the word lines WL increases. To maintain the capacitance ratio in this manner is a large factor for inhibiting the miniaturization of the cell transistor.

Please replace the paragraph at page 12, line 11, with the following rewritten paragraph:

Embodiments of ~~The~~ the present invention will be described hereinafter with reference to the drawings.

Please replace the paragraph at page 12, line 14, with the following rewritten paragraph:

FIGS. 1 and 2A to 2C ~~showing~~ show a cell according to a first embodiment. FIG. 1 is a plan view of the cell, FIG. 2A is a sectional view taken along line 2A-2A of FIG. 1, FIG. 2B is a sectional view taken along line 2B-2B of FIG. 1, and FIG. 2C is a sectional view taken along line 2C-2C of FIG. 1.

Please replace the paragraph at page 25, line 5, with the following rewritten paragraph:

Concretely, for example, it is possible to use a method comprising: forming a metal film in the whole surface; and subsequently selectively etching the metal film to form the word line WL. Alternatively, a method can be used comprising: forming the insulating film in the whole surface; subsequently forming the trench in the insulating film; embedding the metal film in the trench; ~~flattering~~ flattening the metal film by CMP; and forming the word line WL in the trench. Additionally, it is possible to use a method of forming a usual wiring.

Please replace the paragraph at page 39, line 16, with the following rewritten paragraph:

Another exemplary implementation is shown in FIG. 29. As can be seen from FIG. 29, a memory cardholder 80 is provided for receiving a memory card 60 having a semiconductor memory device 50 constituted by the NAND type EEPROM as discussed in each of the embodiments. The cardholder 80 is connected to an electronic device (not shown) and is operable as an interface between the card 60 and the electronic device. The cardholder 80 may perform one or more of the functions of the controller 70 described in connection with FIG. 28.

Please replace the paragraph at page 43, line 16 to page 44, line 2, with the following rewritten paragraph:

The USB memory device 146 transmits a state packet using a state end point (end point 0) in order to inform the host platform 144 of results and states with respect to various operations which have requested by the host platform 144. In this process, the host platform 144 checks if there is any state packet ~~(poling)~~ (polling), and the USB memory device 146 returns an empty packet or the state packet itself, when there is not a packet of a new state message. It is to be noted that the USB cable 148 may be omitted, and a USB connector may also be used to directly connect the USB memory device 146 to the host platform 144. Additionally, various functions of the USB memory device can be carried out.